TLV809 3-Pin Supply Voltage Supervisor

1 Features

- Precision supply voltage monitor: 2.5 V, 3 V, 3.3 V, 5 V
- Power-on reset generator with a fixed delay time of 200 ms
- Supply current: 9 µA (typical)
- Temperature range: -40°C to +85°C
- 3-Pin SOT-23 package
- Pin-for-pin compatible with the MAX809

2 Applications

- Factory automation
- Portable and battery-powered equipment
- Set-top boxes
- Servers
- Appliances
- Electricity meters
- Building automation

3 Description

The TLV809 family of supervisory circuits provides circuit initialization and timing supervision, primarily for digital signal processors (DSPs) and processorbased systems. The newer TLV809E device is a pinto-pin compatible alternative.

During power-on, RESET is asserted when the supply voltage (V_{DD}) becomes greater than 1.1 V. Thereafter, the supervisory circuit monitors V_{DD} and keeps RESET active as long as V_{DD} remains below the threshold voltage, V_{IT} . An internal timer delays the return of the output to the inactive state (high) to ensure proper system reset. The delay time ($t_{d(typ)}$ = 200 ms) starts after V_{DD} rises above the threshold voltage, V_{IT} . When the supply voltage drops below the V_{IT} threshold voltage, the output becomes active (low) again. No external components are required. All devices in this family have a fixed sense-threshold voltage (V_{IT}) set by an internal voltage divider.

This product family is designed for supply voltages of 2.5 V, 3 V, 3.3 V, and 5 V. The circuits are available in a 3-pin SOT-23 package. The TLV809 devices are characterized for operation over a temperature range of -40° C to $+85^{\circ}$ C.

Device Information

Device information				
PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)		
TLV809	SOT-23 (3), DBV	2.90 mm × 1.60 mm		
	SOT-23 (3), DBZ	2.92 mm × 1.30 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Typical Application

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4 Revision History

Changes from Revision E (November 2020) to Revision F (December 2020)

Corrected missed change of VDD from 7 to 6.5 in Absolute Maximum Ratings for all other pins and in note2...

С	Changes from Revision D (March 2016) to Revision E (November 2020)		
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1	
•	Updated the Description section	1	
	Updated Device Comparison		
	Changed VDD from 7 to 6.5 in Absolute Maximum Ratings		
•	Changed V _{OL} @ 500µA from 0.2 to 0.3 in <i>Electrical Characteristics</i>	6	
•	Changed tw pulse duration from 3 to 10µs in <i>Timing Requirements</i>	6	
•	Changed t _{PHL} from 1 to 10µs in Switching Characteristics	6	
	Changed figure from Pulse Duration to V _{OL} , I _{OL} in the Typical Application Section		

		i age
•	Added Device Information table, Pin Configuration and Functions section, ESD Ratings table, Overview section, Feature Description section, Device Functional Modes section, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.	1
•	Deleted pinout drawing from page 1	1
•	Changed Description section: added third paragraph and changed section wording for clarity	1
•	Deleted soldering temperature parameter from Absolute Maximum Ratings table	<mark>5</mark>
•	Changed I _{DD} parameter test conditions in <i>Electrical Characteristics</i> table	<mark>6</mark>
С	hanges from Revision B (September 2010) to Revision C (February 2012)	Page
•	Updated ordering information	4

Changes from Revision C (February 2012) to Revision D (March 2016)

Page

Page

TLV809 SLVSA03F – JUNE 2010 – REVISED DECEMBER 2020

C	hanges from Revision A (July 2010) to Revision B (September 2010)	Page
•	Updated document format to current standards	1
•	Added DBZ package to pinout figure	1
	Added Thermal Information table	
	Changed Figure 7-3	

5 Device Comparison

PRODUCT	THRESHOLD VOLTAGE		
TLV809J25	2.25 V		
TLV809L30	2.64 V		
TLV809K33	2.93 V		
TLV809150	4.55 V		

Table 5-1. Device Threshold Options

Table 5-2. Device Family Comparison

· · · · · · · · · · · · · · · · · · ·		
DEVICE	FUNCTION	
TLV803	Open-Drain, RESET Output	
TLV809	Push-Pull, RESET Output	
TLV810	Push-Pull, RESET Output	

6 Pin Configuration and Functions



Figure 6-1. DBV, DBZ Packages 3-Pin SOT-23 Top View

Pin Functions

PIN NO. NAME		I/O	DESCRIPTION	
2	RESET	0	$\begin{array}{l} \hline \textbf{RESET} \text{ pin. } \textbf{RESET} \text{ is an active low signal, asserting when } V_{DD} \text{ is below the threshold} \\ \textbf{voltage. } When V_{DD} \text{ rises above } V_{IT}, \text{ there is a delay time } (t_d) \text{ until } \textbf{RESET} \text{ deasserts.} \\ \hline \textbf{RESET} \text{ is a push-pull output stage.} \end{array}$	
3	V _{DD}	I	Supply voltage pin. A 0.1- μ F ceramic capacitor from this pin to ground is recommended to improve stability of the threshold voltage.	

7 Specifications 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V	Supply voltage ⁽²⁾		6.5	v
V _{DD}	All other pins ⁽²⁾	-0.3	6.5	v
I _{OL}	Maximum low output current		5	mA
I _{OH}	H Maximum high output current		-5	mA
I _{IK}	Input clamp current ($V_I < 0$ or $V_I > V_{DD}$)		±20	mA
I _{ОК}	Output clamp current ($V_O < 0$ or $V_O > V_{DD}$)		±20	mA
T _A	Operating free-air temperature	-40	85	°C
T _{stg}	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to GND. For reliable operation, do not operate the device at 6.5 V for more than t = 1000h continuously.

7.2 ESD Ratings

				VALUE	UNIT	
V _(ESD) Electrosta	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V		
	Electrostalic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	V		

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

at specified temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{DD}	Supply voltage	2		6	V
C _{IN}	V _{DD} bypass capacitor		0.1		μF
T _A	Operating free-air temperature range	-40		85	°C

7.4 Thermal Information

		TLV809				
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DBZ (SOT-23)	UNIT		
		3 PINS	3 PINS			
R _{0JA}	Junction-to-ambient thermal resistance	242.1	286.9	°C/W		
R _{0JC(top)}	Junction-to-case (top) thermal resistance	213.0	105.6	°C/W		
$R_{\theta JB}$	Junction-to-board thermal resistance	123.4	124.4	°C/W		
Ψ _{JT}	Junction-to-top characterization parameter	45.7	25.8	°C/W		
Ψ _{JB}	Junction-to-board characterization parameter	130.9	107.9	°C/W		
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	_	—	°C/W		

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

7.5 Electrical Characteristics

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT				
			V_{DD} = 2.5 V to 6 V, I _{OH} = -500 µA	V _{DD} – 0.2							
V _{OH}	High-level output voltage		V _{DD} = 3.3 V, I _{OH} = -2 mA	V _{DD} – 0.4			V				
			V _{DD} = 6 V, I _{OH} = -4 mA	V _{DD} – 0.4							
			V _{DD} = 2 V to 6 V, I _{OH} = 500 μA			0.3					
V _{OL} Low-level output voltage			V _{DD} = 3.3 V, I _{OH} = 2 mA			0.4	V				
			V _{DD} = 6 V, I _{OH} = 4 mA			0.4					
	Power-up reset voltage ⁽¹⁾		V _{DD} ≥ 1.1 V, I _{OL} = 50 µA			0.2	V				
		TLV809J25		2.20	2.25	2.30					
	Negative-going input	TLV809L30		2.58	2.64	2.70	v				
V _{IT-}	threshold voltage ⁽²⁾	TLV809K33 $T_A = -40$ C to +05 C		2.87	2.93	2.99	v				
		TLV809150		4.45	4.55	4.65					
		TLV809J25			30						
	Hystoropia	TLV809L30		35			mV				
V _{hys}	Hysteresis	TLV809K33			40		IIIV				
		TLV809150			60						
	Supply ourrent	· ·	V _{DD} = 2 V, RESET is unconnected		9	12					
IDD	Supply current		V _{DD} = 6 V, RESET is unconnected		20	25	μA				
Cı	Input capacitance		$V_{I} = 0 V \text{ to } V_{DD}$		5		pF				

at $T_A = -40^{\circ}$ C to +85°C (unless otherwise noted); typical values are at $T_A = 25^{\circ}$ C

(1) The lowest supply voltage at which $\overline{\text{RESET}}$ becomes active. $t_{r, VDD} \ge 15 \text{ ms/V}$.

(2) To ensure best stability of the threshold voltage, place a bypass capacitor ($0.1-\mu F$ ceramic) near the supply pins.

7.6 Timing Requirements

at T_A = 25°C, R_L = 1 MΩ, and C_L = 50 pF

			MIN	NOM	MAX	UNIT
tw	Pulse duration at V_{DD}	$V_{DD} = V_{IT-} + 0.2 V, V_{DD} = V_{IT-} - 0.2 V$	10			μs

7.7 Switching Characteristics

at $T_A = 25^{\circ}$ C, $R_L = 1 M\Omega$, and $C_L = 50 \text{ pF}$

	PARAMETE	R	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _d	Delay time		$V_{DD} \ge V_{IT-} + 0.2 V$; see Figure 7-1	120	200	280	ms
t _{PHL}	Propagation (delay) time, high-to-low-level output	V _{DD} to RESET delay	V _{IL} = V _{IT-} – 0.2 V, V _{IH} = V _{IT-} + 0.2 V		10		μs

7.8 Timing Diagrams



Figure 7-1. Timing Diagram

7.9 Typical Characteristics



8 Detailed Description

8.1 Overview

The TLV809 is a 3-pin voltage detector with fixed detection thresholds, an active-low push-pull $\overline{\text{RESET}}$ output, and an internal timer to delay the $\overline{\text{RESET}}$ signal when V_{DD} rises above the threshold voltage.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Supply Voltage Monitoring

The device actively monitors its supply voltage to ensure that the power supply is above a certain voltage threshold.

The device offers various fixed threshold options that are approximately 10% below several standard supply voltages (2.5 V, 3.0 V, 3.3 V, 5.0 V).

8.3.2 RESET Output

The device has a RESET output to indicate the status of the input power supply.

RESET is an active low signal, asserting when V_{DD} is below the threshold voltage. When V_{DD} rises above V_{IT} , there is a delay time (t_d) until RESET deasserts.

RESET is a push-pull output stage.

8.4 Device Functional Modes

When the input supply voltage is in its recommended operating range (2 V to 6 V), the device is in a normal operational mode. In normal operational mode the device monitors V_{DD} for undervoltage detection.

When the input supply is below its recommended operating range, the device is in shutdown mode and therefore tries to assert RESET.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

9.1.1 V_{DD} Transient Rejection

The device has built-in rejection of fast transients on the V_{DD} pin. The rejection of transients depends on both the duration and the amplitude of the transient. The amplitude of the transient is measured from the bottom of the transient to the negative threshold voltage of the device, as shown in Figure 9-1.



Figure 9-1. Voltage Transient Measurement

The device does not respond to transients that are fast duration and low amplitude or long duration and small amplitude. Transients meeting or longer than the t_w specified in the Section 7.6 section triggers a reset.

9.1.2 Reset During Power-Up and Power-Down

The device output is valid when V_{DD} is greater than 1.1 V. When V_{DD} is less than 1.1 V, the output transistor turns off and becomes high impedance. The voltage on the RESET pin rises to the voltage level connected to the pullup resistor. Figure 9-2 shows a typical waveform for power-up.



Figure 9-2. Power-Up Response

9.2 Typical Application



Figure 9-3. Monitoring a 3.3-V Supply

9.2.1 Design Requirements

The device must ensure that the supply voltage does not drop more than 15% below 3.3 V. If the supply voltage falls below 3.3 V - 15%, then the load must be disabled.

9.2.2 Detailed Design Procedure

The TLV809K33 is selected to ensure that V_{DD} is greater than 2.87 V when the load is enabled.

9.2.3 Application Curve



Figure 9-4. Low-Level Output Voltage vs Low-Level Output Current

10 Power Supply Recommendations

Power the device with a low-impedance supply. A $0.1-\mu F$ bypass capacitor from V_{DD} to ground is recommended.

11 Layout

11.1 Layout Guidelines

Place the device near the load for the input power supply, with a low-impedance connection to the power supply pins of the load to sense the supply voltage.

11.2 Layout Example



Figure 11-1. Example Layout

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

TLV803 Data Sheet, SBVS157

TLV810 Data Sheet, SBVS158

12.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.3 Trademarks

TI E2E[™] is a trademark of Texas Instruments. All trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV809I50DBVR	ACTIVE	SOT-23	DBV	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTBI	Samples
TLV809I50DBVT	ACTIVE	SOT-23	DBV	3	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTBI	Samples
TLV809I50DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMV	Samples
TLV809I50DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMV	Samples
TLV809J25DBVR	ACTIVE	SOT-23	DBV	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTCI	Samples
TLV809J25DBVT	ACTIVE	SOT-23	DBV	3	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTCI	Samples
TLV809J25DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMT	Samples
TLV809J25DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMT	Samples
TLV809K33DBVR	ACTIVE	SOT-23	DBV	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTRI	Samples
TLV809K33DBVT	ACTIVE	SOT-23	DBV	3	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTRI	Samples
TLV809K33DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMX	Samples
TLV809K33DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMX	Samples
TLV809L30DBVR	ACTIVE	SOT-23	DBV	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTXI	Samples
TLV809L30DBVT	ACTIVE	SOT-23	DBV	3	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VTXI	Samples
TLV809L30DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMZ	Samples
TLV809L30DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 85	BCMZ	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect. NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

PACKAGE OPTION ADDENDUM

13-Jul-2021

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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3-Jun-2022

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal					1		r					. <u> </u>
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV809I50DBVR	SOT-23	DBV	3	3000	180.0	9.0	3.3	3.2	1.47	4.0	8.0	Q3
TLV809I50DBVT	SOT-23	DBV	3	250	180.0	9.0	3.3	3.2	1.47	4.0	8.0	Q3
TLV809I50DBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809I50DBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV809I50DBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV809I50DBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809J25DBVR	SOT-23	DBV	3	3000	180.0	9.0	3.3	3.2	1.47	4.0	8.0	Q3
TLV809J25DBVT	SOT-23	DBV	3	250	180.0	9.0	3.3	3.2	1.47	4.0	8.0	Q3
TLV809J25DBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809J25DBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV809J25DBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV809K33DBVR	SOT-23	DBV	3	3000	178.0	9.0	3.3	3.2	1.47	4.0	8.0	Q3
TLV809K33DBVT	SOT-23	DBV	3	250	178.0	8.4	3.3	3.2	1.47	4.0	8.0	Q3
TLV809K33DBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV809K33DBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809K33DBZT	SOT-23	DBZ	3	250	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

3-Jun-2022

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV809K33DBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV809L30DBVR	SOT-23	DBV	3	3000	180.0	9.0	3.3	3.2	1.47	4.0	8.0	Q3
TLV809L30DBVT	SOT-23	DBV	3	250	180.0	9.0	3.3	3.2	1.47	4.0	8.0	Q3
TLV809L30DBZR	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TLV809L30DBZR	SOT-23	DBZ	3	3000	178.0	9.0	3.15	2.77	1.22	4.0	8.0	Q3
TLV809L30DBZT	SOT-23	DBZ	3	250	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

3-Jun-2022



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV809I50DBVR	SOT-23	DBV	3	3000	182.0	182.0	20.0
TLV809I50DBVT	SOT-23	DBV	3	250	182.0	182.0	20.0
TLV809I50DBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV809I50DBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV809I50DBZT	SOT-23	DBZ	3	250	203.0	203.0	35.0
TLV809I50DBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0
TLV809J25DBVR	SOT-23	DBV	3	3000	182.0	182.0	20.0
TLV809J25DBVT	SOT-23	DBV	3	250	182.0	182.0	20.0
TLV809J25DBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV809J25DBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV809J25DBZT	SOT-23	DBZ	3	250	200.0	183.0	25.0
TLV809K33DBVR	SOT-23	DBV	3	3000	180.0	180.0	18.0
TLV809K33DBVT	SOT-23	DBV	3	250	180.0	180.0	18.0
TLV809K33DBZR	SOT-23	DBZ	3	3000	203.0	203.0	35.0
TLV809K33DBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV809K33DBZT	SOT-23	DBZ	3	250	180.0	180.0	18.0
TLV809K33DBZT	SOT-23	DBZ	3	250	203.0	203.0	35.0
TLV809L30DBVR	SOT-23	DBV	3	3000	182.0	182.0	20.0

PACKAGE MATERIALS INFORMATION

3-Jun-2022

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV809L30DBVT	SOT-23	DBV	3	250	182.0	182.0	20.0
TLV809L30DBZR	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TLV809L30DBZR	SOT-23	DBZ	3	3000	180.0	180.0	18.0
TLV809L30DBZT	SOT-23	DBZ	3	250	203.0	203.0	35.0

DBV0003A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

DBV0003A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

DBV0003A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

SOT-23 - 1.12 mm max height SMALL OUTLINE TRANSISTOR



DBZ0003A



PACKAGE OUTLINE

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC registration TO-236, except minimum foot length.

DBZ0003A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

Publication IPC-7351 may have alternate designs.
 Solder mask tolerances between and around signal pads can vary based on board fabrication site.

DBZ0003A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

^{6.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{7.} Board assembly site may have different recommendations for stencil design.